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# Short channel GaN FET MMIC technology for high reliability applications



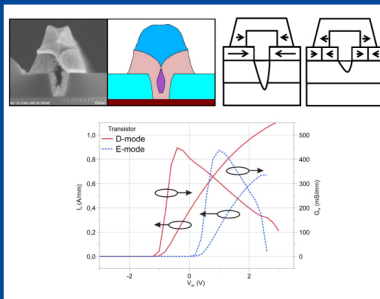
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Forschungsberichte aus dem

Ferdinand-Braun-Institut,  
Leibniz-Institut  
für Höchstfrequenztechnik

Innovationen mit Mikrowellen & Licht

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